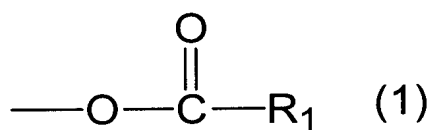


Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An underlayer coating forming composition comprising a crosslinking compound, an organic solvent and a dextrin ester compound,

wherein at least 50% of hydroxy groups in dextrin are converted into ester groups of formula (1):



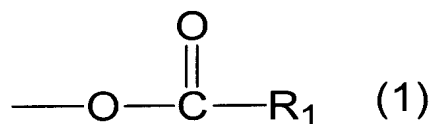
wherein R₁ is C₁₋₁₀alkyl group that may be substituted with a hydroxy group, a carboxyl group, a cyano group, a nitro group, a C₁₋₆alkoxy group, a fluorine atom, a chlorine atom, a bromine atom, an iodine atom or a C₁₋₆alkoxycarbonyl group; or a phenyl group, a naphthyl group or an anthryl group, each of which may be substituted with a C₁₋₆alkyl group, a hydroxy group, a carboxyl group, a cyano group, a nitro group, a C₁₋₆alkoxy group, a fluorine atom, a chlorine atom, a bromine atom, an iodine atom or a C₁₋₆alkoxycarbonyl group,

wherein the crosslinking compound has two or more crosslink-forming substituents selected from the group consisting of an isocyanate group, an epoxy group, a hydroxymethylamino group and an alkoxymethylamino group, and

wherein the underlayer coating composition forms an underlayer coating of a photoresist in a lithography process.

2. (Currently Amended) An underlayer coating forming composition comprising a crosslinking compound, an organic solvent and a dextrin ester compound,

wherein at least 50% of hydroxy groups in dextrin is converted into ester groups of formula (1):



wherein R₁ is a C₁₋₁₀alkyl group that may be substituted with a hydroxy group, a carboxyl group, a cyano group, a nitro group, a C₁₋₆alkoxy group, a fluorine atom, a chlorine atom, a bromine atom, an iodine atom or a C₁₋₆alkoxycarbonyl group; or a phenyl group, a naphthyl group or an anthryl group, each of which may be substituted with C₁₋₆alkyl group, hydroxy group, carboxyl group, cyano group, nitro group, C₁₋₆alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C₁₋₆alkoxycarbonyl group,

wherein the dextrin ester compound has a weight average molecular weight of 4000 to 20000,

wherein the crosslinking compound has two or more crosslink-forming substituents selected from the group consisting of an isocyanate group, an epoxy group, a hydroxymethylamino group and an alkoxymethylamino group, and

wherein the underlayer coating composition forms an underlayer coating of a photoresist in a lithography process..

3. (Previously Presented) The underlayer coating forming composition according to claim 1, further comprising an acid compound or an acid generator.

4. (Previously Presented) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising:

coating the underlayer coating forming composition according to claim 1 on a semiconductor substrate, and baking it to form the underlayer coating;

forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.

5. (Previously Presented) The underlayer coating forming composition according to claim 1, wherein the composition forms the underlayer coating by coating the composition on a semiconductor substrate having a hole with an aspect ratio shown in height/diameter of 1 or more, and baking it.

6. (Previously Presented) The underlayer coating forming composition according to claim 2, further comprising an acid compound or an acid generator.

7. (Previously Presented) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising:

coating the underlayer coating forming composition according to claim 2 on a semiconductor substrate, and baking it to form the underlayer coating;

forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.

8. (Previously Presented) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising:

coating the underlayer coating forming composition according to claim 3 on a semiconductor substrate, and baking it to form the underlayer coating;

forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.

9. (Previously Presented) The underlayer coating forming composition according to claim 2, wherein the composition forms the underlayer coating by coating the composition on a semiconductor substrate having a hole with an aspect ratio shown in height/diameter of 1 or more, and baking it.

10. (Previously Presented) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising:

coating the underlayer coating forming composition according to claim 6 on a semiconductor substrate, and baking it to form the underlayer coating;

forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.